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 <i>C30B 15/30</i> (2006.01) <i>C30B 30/04</i> (2006.01)</p> <p>(21) International Application Number:
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- (54) Title:** SYSTEMS AND METHODS FOR PRODUCTION OF SILICON USING A HORIZONTAL MAGNETIC FIELD

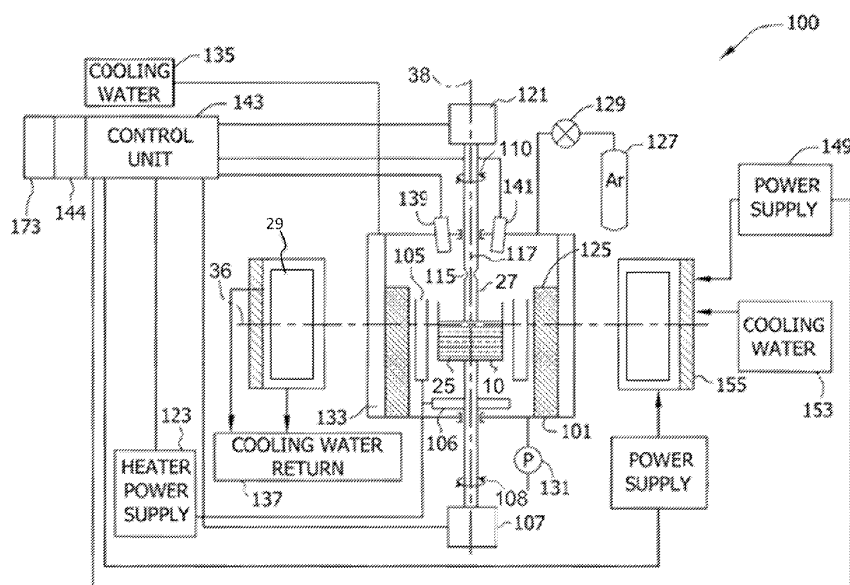


FIG. 4

- (57) Abstract:** A method for producing a silicon ingot by the horizontal magnetic field Czochralski method includes rotating a crucible containing a silicon melt, applying a horizontal magnetic field to the crucible, contacting the silicon melt with a seed crystal, and withdrawing the seed crystal from the silicon melt while rotating the crucible to form a silicon ingot. The crucible has a wettable surface with a cristobalite layer formed thereon.

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